

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449B/PTO
**INFORMATION DISCLOSURE
 STATEMENT BY APPLICANT**

Date Submitted: October 17, 2005

(use as many sheets as necessary)

Complete if Known

10/553416

Sheet 1 of 1

Application Number	Unassigned
Filing Date	10/17/2005
First Named Inventor	Tadaihiro OHMI
Group Art Unit	Unassigned
Examiner Name	Unassigned
Attorney Docket Number	039262-0143

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
/T.T./	A1	6,399,520	B1	KAWAKAMI et al.	06-04-2002	

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Documents	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Office ³	Number ⁴	Kind Code ⁵ (if known)				
/T.T./	A2	JP	2002-343961	A	SONY CORP.	11-29-2002		
/T.T./	A3	JP	2000-294550	A	TOKYO ELECTRON LTD.	10-20-2000		

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ⁶
/T.T./	A4	M. SATO et al., "Rapid Oxidation of SiC Using Microwave-Discharged O ₂ Plasma at Low Temperatures (<300°C)," Jap. J. of Applied Physics, Part 2, March 1, 2002, Vol. 41:3A, pp. L233-L235.	
/T.T./	A5	A. GOLZ et al., "Plasma-assisted formation of low defect density SiC-SiO ₂ interfaces," J. of Vacuum Science and Technology B, 1997, Vol. 15:4, pp. 1097-1104.	

Examiner Signature

/Thien Tran/

Date Considered

10/23/2008

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Unique citation designation number. ² See attached Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document.

⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450